PNP Silicon General Purpose Amplifier Transistor

This PNP transistor is designed for general purpose amplifier applications. This device is housed in the SOT-723 package which is designed for low power surface mount applications, where board space is at a premium.

Features

- Reduces Board Space
- High h_{FE}, 210–460 (Typical)
- Low $V_{CE(sat)}$, < 0.5 V
- ESD Performance: Human Body Model; > 2000 V,

Machine Model; > 200 V

- Available in 4 mm, 8000 / Tape & Reel
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free Devices

MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

Rating	Symbol	Value	Unit
Collector-Base Voltage	V _{(BR)CBO}	-60	Vdc
Collector–Emitter Voltage	V _{(BR)CEO}	-50	Vdc
Emitter-Base Voltage	$V_{(BR)EBO}$	-6.0	Vdc
Collector Current – Continuous	Ic	-100	mAdc

THERMAL CHARACTERISTICS

Rating	Symbol	Max	Unit
Power Dissipation (Note 1)	P_{D}	265	mW
Junction Temperature	TJ	150	°C
Storage Temperature Range	T _{stg}	-55 ~ + 150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

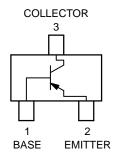
 Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint.



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PNP GENERAL PURPOSE AMPLIFIER TRANSISTORS SURFACE MOUNT



MARKING DIAGRAM



SOT-723 CASE 631AA



F9 = Specific Device Code M = Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
2SA2029M3T5G	SOT-723 (Pb-Free)	8000 / Tape & Reel
NSV2SA2029M3T5G	SOT-723 (Pb-Free)	8000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C)

Characteristic	Symbol	Min	Тур	Max	Unit
Collector–Base Breakdown Voltage (I _C = -50 μAdc, I _E = 0)	V _{(BR)CBO}	-60	-	-	Vdc
Collector–Emitter Breakdown Voltage (I _C = -1.0 mAdc, I _B = 0)	V _{(BR)CEO}	-50	-	-	Vdc
Emitter–Base Breakdown Voltage ($I_E = -50 \mu Adc$, $I_E = 0$)	V _{(BR)EBO}	-6.0	-	-	Vdc
Collector–Base Cutoff Current (V _{CB} = -30 Vdc, I _E = 0)	Ісво	-	-	-0.5	nA
Emitter-Base Cutoff Current (V _{EB} = -7.0 Vdc, I _B = 0)	I _{EBO}	-	-	-0.1	μΑ
Collector–Emitter Saturation Voltage (Note 2) (I _C = -50 mAdc, I _B = -5.0 mAdc)	V _{CE(sat)}	-	-	-0.5	Vdc
DC Current Gain (Note 2) (V _{CE} = -6.0 Vdc, I _C = -1.0 mAdc)	h _{FE}	120	-	560	-
Transition Frequency ($V_{CE} = -12 \text{ Vdc}, I_{C} = -2.0 \text{ mAdc}, f = 30 \text{ MHz}$)	f⊤	_	140	_	MHz
Output Capacitance (V _{CB} = -12 Vdc, I _E = 0 Adc, f = 1.0 MHz)	C _{OB}	-	3.5	_	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2%.

TYPICAL ELECTRICAL CHARACTERISTICS

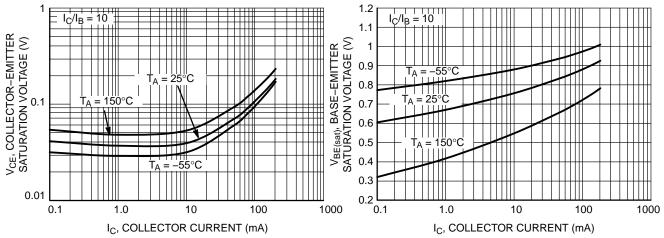


Figure 1. Collector–Emitter Saturation Voltage vs. Collector Current

Figure 2. Base-Emitter Saturation Voltage vs. Collector Current

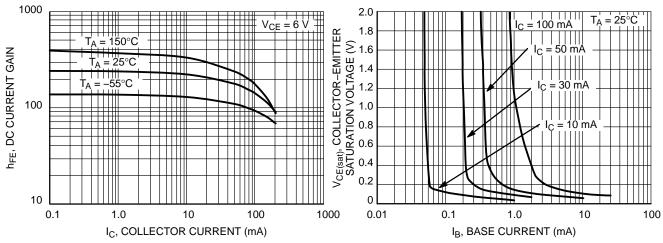


Figure 3. DC Current Gain vs. Collector Current

Figure 4. Saturation Region

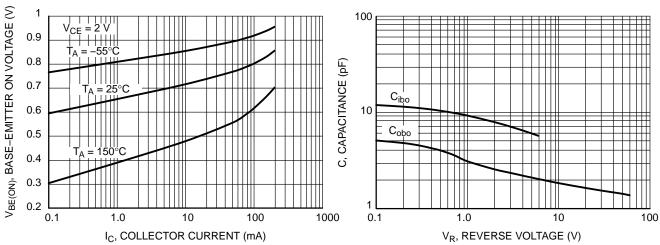


Figure 5. Base–Emitter Turn–ON Voltage vs. Collector Current

Figure 6. Capacitance

TYPICAL ELECTRICAL CHARACTERISTICS

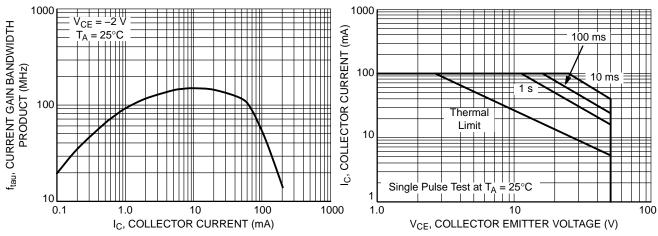


Figure 7. Current Gain Bandwidth Product vs. Collector Current

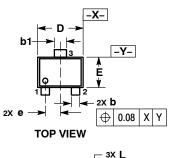
Figure 8. Safe Operating Area

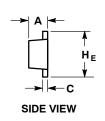


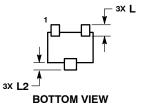


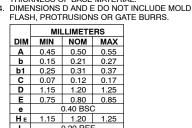
SOT-723 CASE 631AA ISSUE D

DATE 10 AUG 2009









NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD

FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

RECOMMENDED SOLDERING FOOTPRINT*

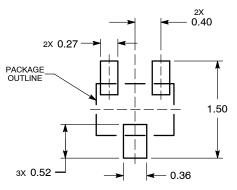
0.20 0.25





XX = Specific Device Code M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
EMITTER	2. N/C	2. ANODE	CATHODE	SOURCE
COLLECTOR	CATHODE	CATHODE	ANODE	3. DRAIN

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